

METHODS FOR FORMING CONDUCTIVE STRUCTURES
AND STRUCTURES REGARDING SAME

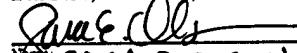
Abstract of the Invention

A method for forming a metal/metal oxide structure that includes forming metal
5 oxide regions, e.g., ruthenium oxide regions, at grain boundaries of a metal layer, e.g.,
platinum. Preferably, the metal oxide regions are formed by diffusion of oxygen
through grain boundaries of the metal layer, e.g., platinum, to oxidize a metal layer
thereon, e.g., ruthenium layer. The structure is particularly advantageous for use in
capacitor structures and memory devices, such as dynamic random access memory
10 (DRAM) devices.

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